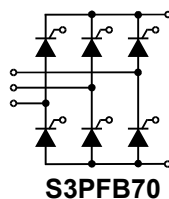
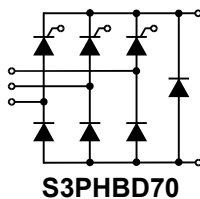
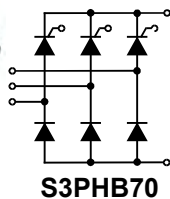
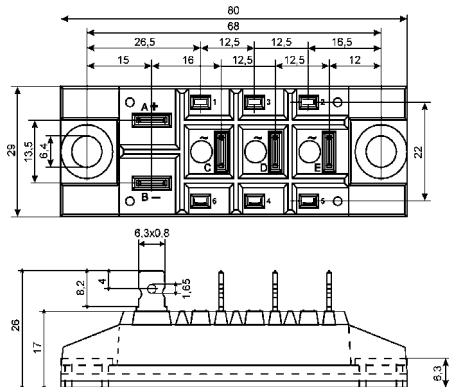


S3PHB70, S3PHBD70, S3PFB70

Three Phase Half Controlled Bridge Modules/Full Controlled Bridge



Dimensions in mm (1mm=0.0394")



Type	V_{RSM} V	V_{RRM} V
S3PHB70G08B S3PHBD70G08B S3PFB70G08B	900	800
S3PHB70G12B S3PHBD70G12B S3PFB70G12B	1300	1200
S3PHB70G14B S3PHBD70G14B S3PFB70G14B	1500	1400
S3PHB70G16B S3PHBD70G16B S3PFB70G16B	1700	1600

Symbol	Test Conditions		Maximum Ratings	Unit
I_{dav} I_{davm} I_{FRMS}, I_{TRMS}	Tc=85°C, module module per leg		70 70 36	A
I_{FSM}, I_{TSM}	$T_{VJ}=45^{\circ}C$ $V_R=0$	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	550 600	A
	$T_{VJ}=T_{VJM}$ $V_R=0$	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	500 550	
I^2t	$T_{VJ}=45^{\circ}C$ $V_R=0$	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	1520 1520	A ² s
	$T_{VJ}=T_{VJM}$ $V_R=0$	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	1250 1250	
$(di/dt)_{cr}$	$T_{VJ}=125^{\circ}C$ f=50Hz, t _p =200us V _D =2/3V _{DRM} I _G =0.3A diG/dt=0.3A/us	repetitive, I _T =50A non repetitive, I _T =1/2 · I _{dav}	150 500	A/us
$(dv/dt)_{cr}$	$T_{VJ}=T_{VJM}$; R _{GK} = ∞; method 1 (linear voltage rise)	V _{DR} =2/3V _{DRM}	1000	V/us
P_{GM}	$T_{VJ}=T_{VJM}$ I _T =I _{TAVM}	t _p =30us t _p =500us t _p = 10ms	10 5 1	W
T_{VJ} T_{VJM} T_{stg}			-40...+125 125 -40...+125	°C
V_{ISOL}	50/60Hz, RMS I _{ISOL} ≤1mA	t=1min t=1s	2500 3000	V~
M_d	Mounting torque (M5) (10-32 UNF)		5 ± 15 % 44 ± 15 %	Nm/lb.in.
Weight	typical		95	g

Sirectifier®

S3PHB70, S3PHBD70, S3PFB70

Three Phase Half Controlled Bridge Modules/Full Controlled Bridge

Symbol	Test Conditions	Characteristic Values	Unit
$I_{d,IR}$	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	5	mA
V_{TM}/V_{FM}	$I_{TM}, I_{FM}=70A; T_{VJ}=25^{\circ}C$ for every chip	1.64	V
V_{TO}	For power-loss calculations only	0.85	V
r_T		11	m Ω
V_{GT}	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
I_{GT}	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	100 200	mA
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.2	V
I_{GD}		5	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=10\mu s$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	450	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	200	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	2	μs
t_q	$T_{VJ}=T_{VJM}; I_T=20A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=15V/\mu s; V_D=2/3V_{DRM}$ typ.	250	μs
I_{RM}		45	A
R_{thJC}	per thyristor/diode; DC current per module	0.9 0.15	K/W
R_{thJK}	per thyristor/diode; DC current per module	1.1 0.157	K/W
ds	Creeping distance on surface	16.1	mm
da	Strike distance through air	7.5	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * Low forward voltage drop
- * Package with copper base plate
- * Glass passivated chips
- * Isolation voltage 3000 V~
- * 1/4" fast-on power terminals
- * UL File NO.E310749
- * RoHS compliant

APPLICATIONS

- * Input rectifiers for PWM inverter
- * Supplies for DC power equipment
- * Field supply for DC motors
- * Battery DC power supplies

ADVANTAGES

- * Space and weight savings
- * Easy to mount with two screws
- * Improved temperature and power cycling capability
- * Small and light weight

Sirectifier®